	Application No.	cation No. Applicant(s)		
	09/921,423	THAKUR ET AL.A	THAKUR ET AL A	
Notice of Allowability	Examiner	Art Unit		
	Johannes P Mondt	2826	l go	
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIG	(OR REMAINS) CLOSED in or other appropriate communication is su	this application. If not includ nication will be mailed in due	ed course. THIS	
1. This communication is responsive to After-Final Amendment	nt filed 7/13/04.		·	
2. The allowed claim(s) is/are 1-9 and 11-12.				
3. \square The drawings filed on <u>17 March 2003</u> are accepted by the E	Examiner.			
 4. ☐ Acknowledgment is made of a claim for foreign priority unappriority and all blue blue blue blue blue blue blue bl		r (f).		
2. Certified copies of the priority documents have		n No		
3. Copies of the certified copies of the priority doc	cuments have been received	in this national stage applica	ation from the	
International Bureau (PCT Rule 17.2(a)).				
* Certified copies not received:				
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the re	quirements	
5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give			NOTICE OF	
6. CORRECTED DRAWINGS (as "replacement sheets") must	t be submitted.			
(a) including changes required by the Notice of Draftsperso		(PTO-948) attached		
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date				
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment or i	n the Office action of		
Identifying indicia such as the application number (see 37 CFR 1.8 each sheet. Replacement sheet(s) should be labeled as such in the			e back) of	
7. DEPOSIT OF and/or INFORMATION about the depos attached Examiner's comment regarding REQUIREMENT F	sit of BIOLOGICAL MATE FOR THE DEPOSIT OF BIO	RIAL must be submitted. I LOGICAL MATERIAL.	Note the	
Attachment(s)				
1. Notice of References Cited (PTO-892)		5. Notice of Informal Patent Application (PTO-152)		
2. Notice of Draftperson's Patent Drawing Review (PTO-948)		6. ☐ Interview Summary (PTO-413), Paper No./Mail Date		
3. Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date		mendment/Comment		
4. Examiner's Comment Regarding Requirement for Deposit	8. 🛛 Examiner's S	Statement of Reasons for Allo	wance	
of Biological Material	9. 🗌 Other	· cbml	honton	
		Minhloa Primary E Art Unit	xaminer	

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04)

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Attorney J. Duzan on July 26, 2004.

BEGIN EXAMINER'S AMENDMENT

Claim 11: the wording "said at least one dielectric layer" (lines 1-2) has been replaced by "said at least one layer of dielectric material".

Claim 12: the wording "said conductive layer" (lines 1-2) has been replaced by "said at least one electrode layer".

END EXAMINER'S AMENDMENT

REASONS FOR ALLOWANCE

Claims 1-9 and 11-12 are allowed.

1. The following is an examiner's statement of reasons for allowance:

a semiconductor memory device with capacitor cell wherein at least one layer of germanium boro-phospho silicate glass has a portion that is in contact with a layer of boro-phospho silicate glass has not been found in the prior art. Although semiconductor memory device with capacitor cell including either boro-phospho silicate glass or germanium boro-phospho silicate glass as materials along roughened interfaces are known (see, e.g., Ando (6,097,053) or Sandhu et al (6,249,019 B1)), and although

exploitation of differences in etch rates between abutting layers of silicon oxide layers of different densities in said capacitor cell are known to have been used for creating corrugation and thus yielding enhanced capacitance as witnessed by Hsia et al (5,827,783), the known sensitivity in the dependence of etch rate on germanium content of boro-phospho silicate glass (see Haller (5,804,506), i.e., on compositional differences between the abutting layers, does not appear to have been exploited in accordance with claims by Applicant.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Johannes P Mondt whose telephone number is 571-272-1919. The examiner can normally be reached on 8:00 - 18:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J Flynn can be reached on 571-272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

JPM July 23,2004